

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE ( $\pi$ -MOS V)

# 2SK2598

HIGH SPEED, HIGH VOLTAGE SWITCHING APPLICATIONS

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

- Low Drain-Source ON Resistance :  $R_{DS(ON)} = 0.18 \Omega$  (Typ.)
- High Forward Transfer Admittance :  $|Y_{fs}| = 13 S$  (Typ.)
- Low Leakage Current :  $I_{DSS} = 100 \mu A$  (Max.) ( $V_{DS} = 250 V$ )
- Enhancement-Mode :  $V_{th} = 1.5 \sim 3.5 V$  ( $V_{DS} = 10 V, I_D = 1 mA$ )

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		$V_{DSS}$	250	V
Drain-Gate Voltage ( $R_{GS} = 20 k\Omega$ )		$V_{DGR}$	250	V
Gate-Source Voltage		$V_{GSS}$	$\pm 20$	V
Drain Current	DC	$I_D$	13	A
	Pulse	$I_{DP}$	52	
Drain Power Dissipation ( $T_c = 25^\circ C$ )		$P_D$	60	W
Single Pulse Avalanche Energy**		$E_{AS}$	148	mJ
Avalanche Current		$I_{AR}$	13	A
Repetitive Avalanche Energy*		$E_{AR}$	6	mJ
Channel Temperature		$T_{ch}$	150	$^\circ C$
Storage Temperature Range		$T_{stg}$	$-55 \sim 150$	$^\circ C$

**THERMAL CHARACTERISTICS**

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	2.08	$^\circ C / W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	83.3	$^\circ C / W$

Note ;

\* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

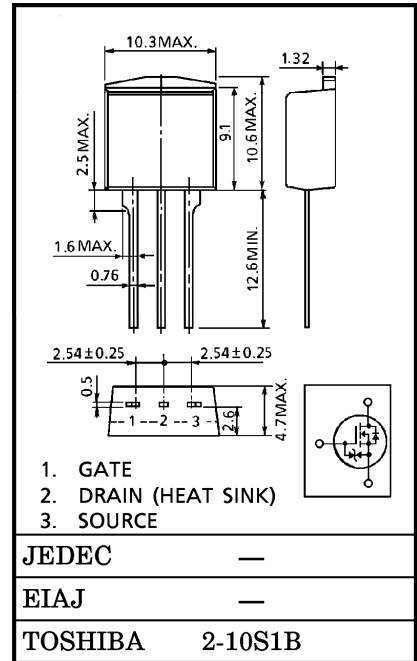
\*\*  $V_{DD} = 50 V$ , Starting  $T_{ch} = 25^\circ C$ ,  $L = 1.48 mH$ ,  $R_G = 25 \Omega$ ,  $I_{AR} = 13 A$

**This transistor is an electrostatic sensitive device. Please handle with caution.**

**INDUSTRIAL APPLICATIONS**

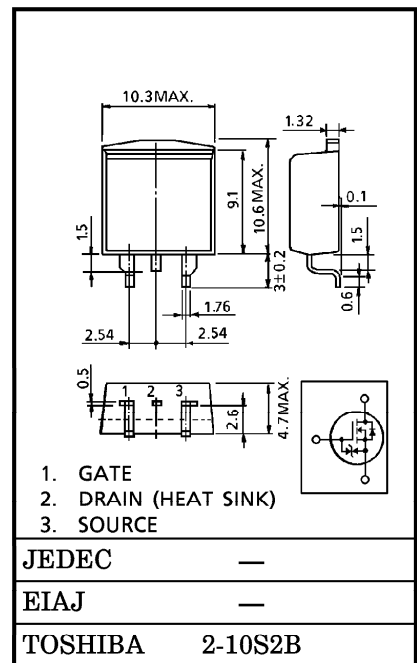
TO-220FL

Unit in mm



TO-220SM

Unit in mm



Weight : 1.5 g

961001EAA2

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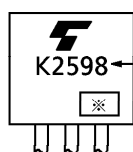
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current	$I_{GSS}$	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$	
Drain Cut-off Current	$I_{DSS}$	$V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	$\mu\text{A}$	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	250	—	—	V	
Gate Threshold Voltage	$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.5	—	3.5	V	
Drain-Source ON Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 6.5\text{ A}$	—	0.18	0.25	$\Omega$	
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 6.5\text{ A}$	6	13	—	S	
Input Capacitance	$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$	—	1800	—	pF	
Reverse Transfer Capacitance	$C_{rss}$		—	130	—		
Output Capacitance	$C_{oss}$		—	500	—		
Switching Time	Rise Time	$t_r$		—	15	—	ns
	Turn-on Time	$t_{on}$		—	25	—	
	Fall Time	$t_f$		—	10	—	
	Turn-off Time	$t_{off}$		—	70	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)	$Q_g$	$V_{DD} \approx 200\text{ V}, V_{GS} = 10\text{ V},$ $I_D = 13\text{ A}$	—	40	—	nC	
Gate-Source Charge	$Q_{gs}$		—	25	—		
Gate-Drain ("Miller") Charge	$Q_{gd}$		—	15	—		

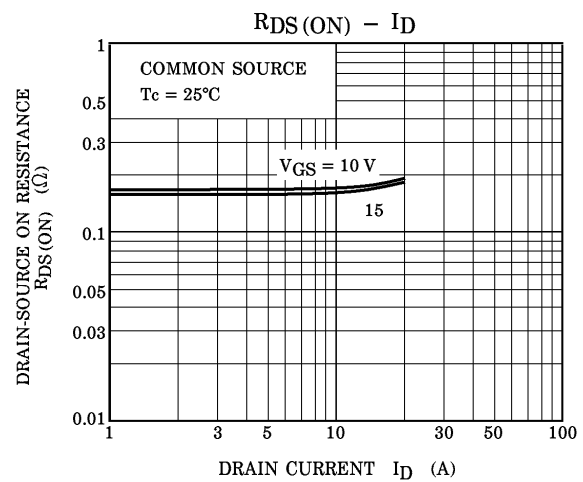
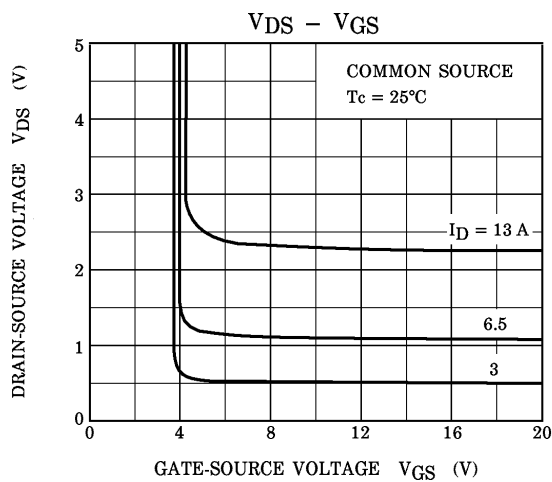
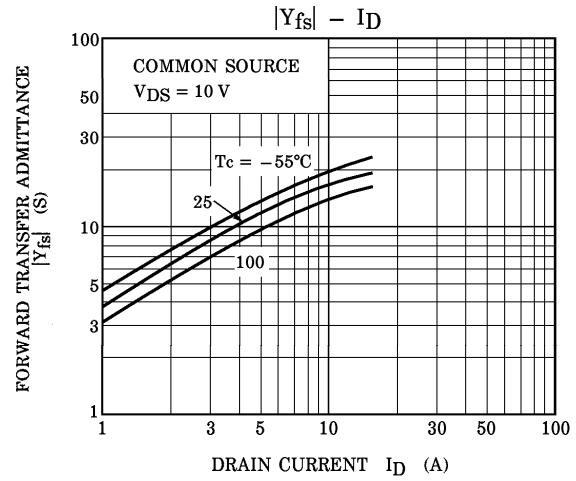
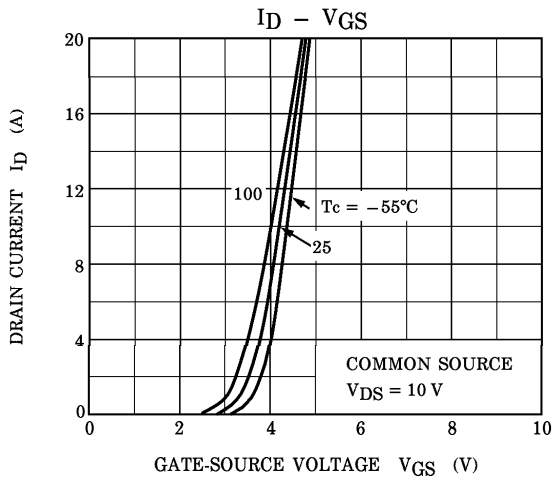
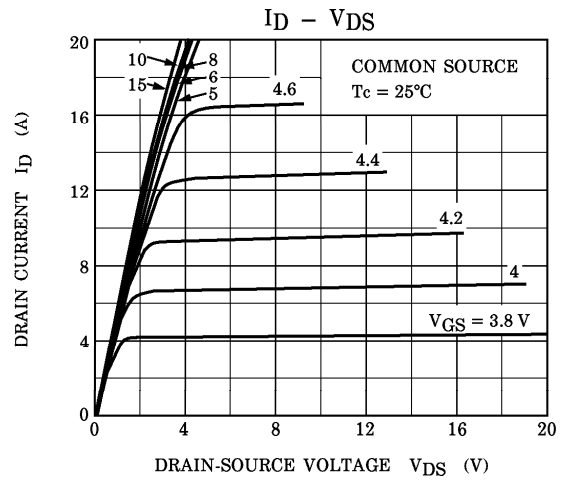
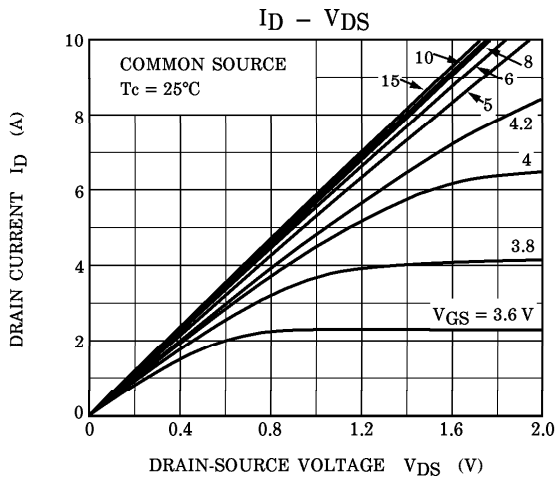
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

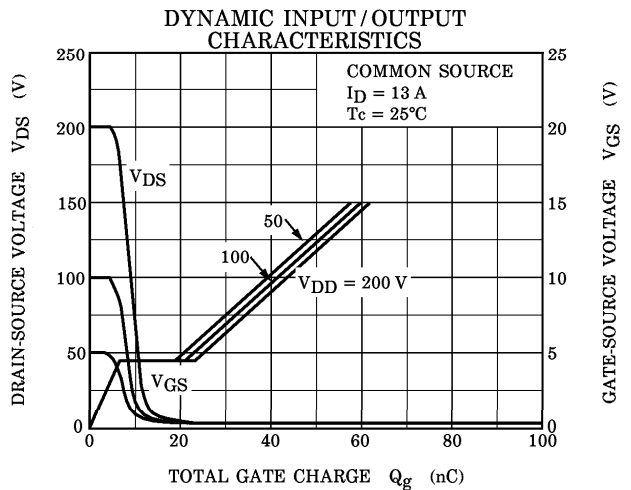
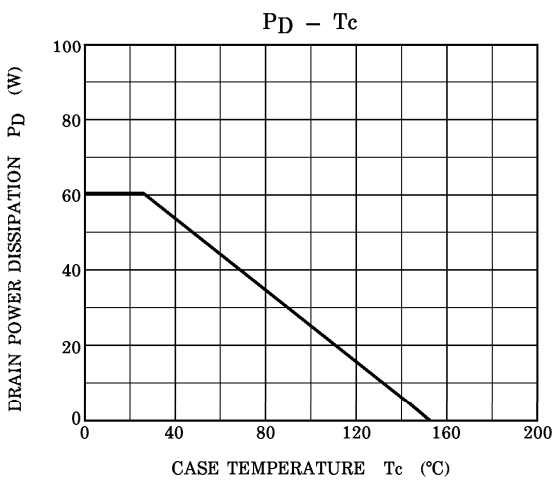
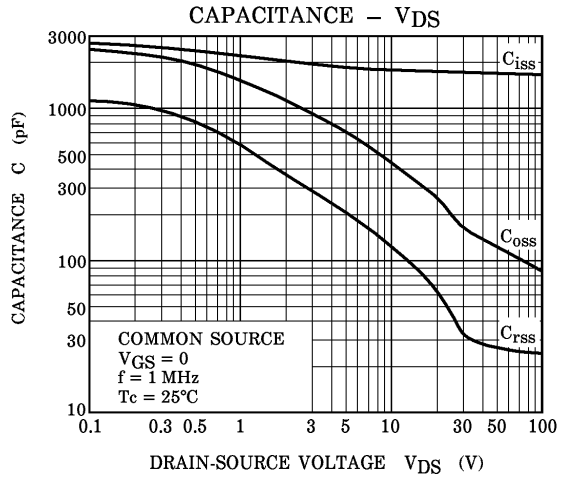
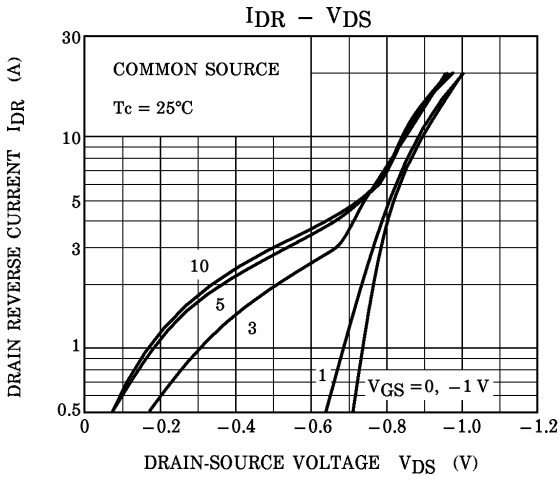
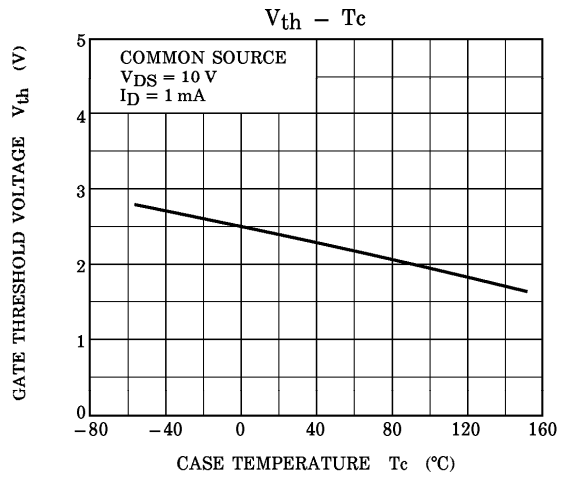
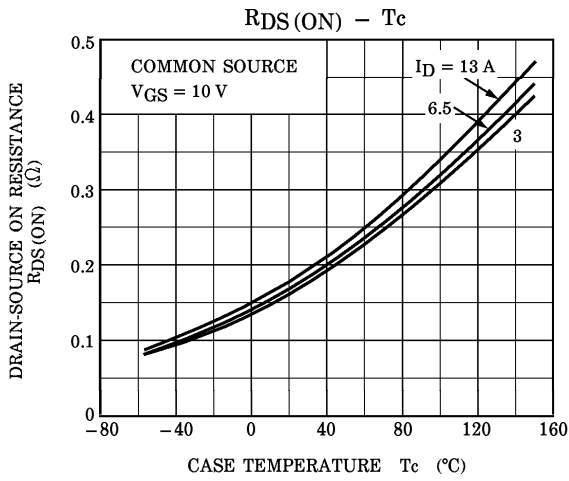
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	$I_{DR}$	—	—	—	13	A
Pulse Drain Reverse Current	$I_{DRP}$	—	—	—	52	A
Diode Forward Voltage	$V_{DSF}$	$I_{DR} = 13\text{ A}, V_{GS} = 0\text{ V}$	—	—	-2.0	V
Reverse Recovery Time	$t_{rr}$	$I_{DR} = 13\text{ A}, V_{GS} = 0\text{ V}$	—	260	—	ns
Reverse Recovery Charge	$Q_{rr}$	$dI_{DR}/dt = 100\text{ A}/\mu\text{s}$	—	0.3	—	$\mu\text{C}$

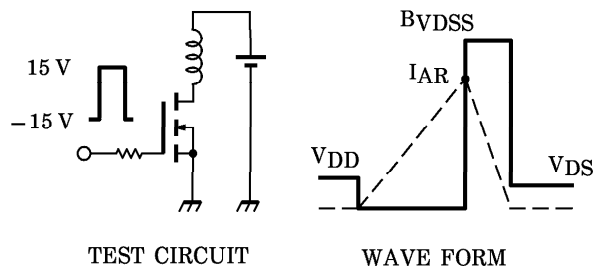
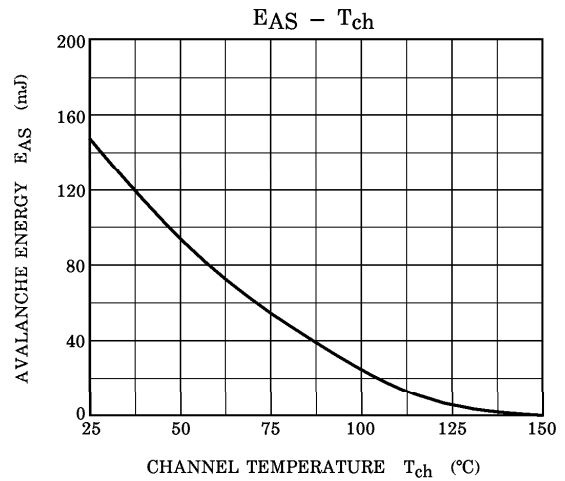
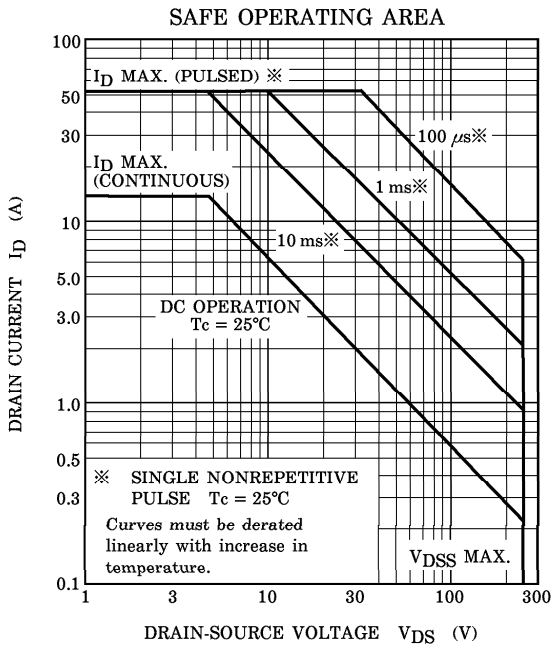
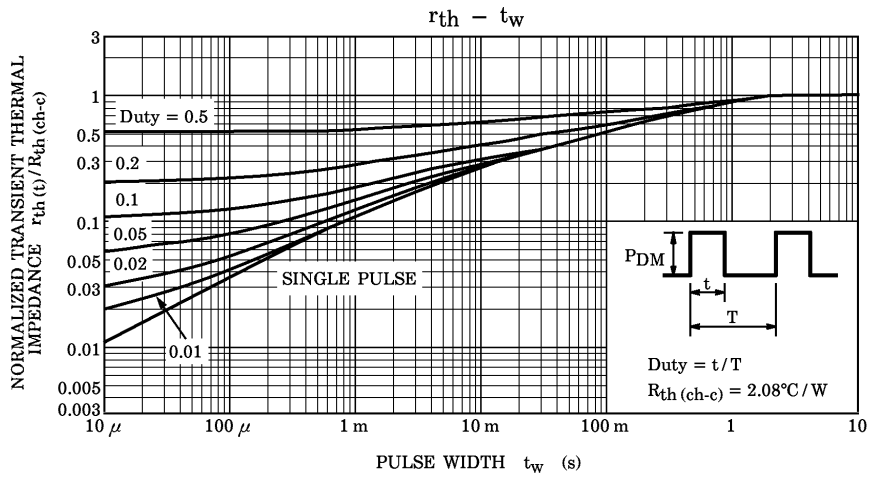
MARKING



TYPE  
 ※ Lot Number  
 □ □ — Month (Starting from Alphabet A)  
 — Year (Last Number of the Christian Era)







Peak  $I_{AR} = 13 \text{ A}$ ,  $R_G = 25 \Omega$   
 $V_{DD} = 50 \text{ V}$ ,  $L = 1.48 \text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$